1. General description

The 74LVC1G10 provides a low-power, low-voltage single 3-input NAND gate.

The inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall time.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - JESD8-B/JESD36 (2.7 V to 3.6 V).
- ± 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1.Ordering	information							
Type number	Package							
	Temperature range	Name	Description	Version				
74LVC1G10GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363				
74LVC1G10GV	–40 °C to +125 °C	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457				
74LVC1G10GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1.45 \times 0.5$ mm	SOT886				
74LVC1G10GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1 \times 0.5$ mm	SOT891				
74LVC1G10GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115				
74LVC1G10GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202				

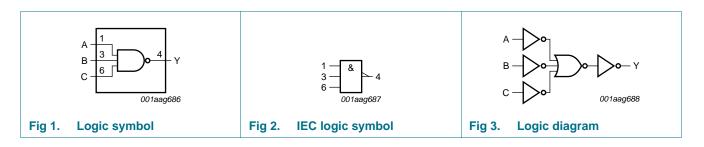
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74LVC1G10GW	YM
74LVC1G10GV	YM
74LVC1G10GM	YM
74LVC1G10GF	YM
74LVC1G10GN	YM
74LVC1G10GS	YM

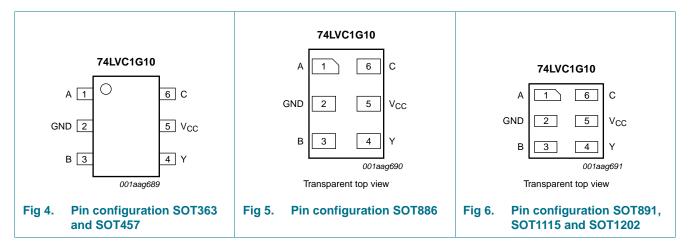
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

SymbolPinDescriptionA1data inputGND2ground (0 V)B3data inputY4data outputV _{CC} 5supply voltageC6data input	Table 3.	Pin description	
GND2ground (0 V)B3data inputY4data outputV _{CC} 5supply voltage	Symbol	Pin	Description
B3data inputY4data outputV _{CC} 5supply voltage	А	1	data input
Y4data outputV _{CC} 5supply voltage	GND	2	ground (0 V)
V _{CC} 5 supply voltage	В	3	data input
	Y	4	data output
C 6 data input	V _{CC}	5	supply voltage
	С	6	data input

7. Functional description

Table 4. Function table^[1]

Input	Output		
Α	В	C	Y
Н	Н	Н	L
L	Х	Х	Н
Х	L	Х	Н
X	Х	L	Н

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

			•	10	,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
I _{OK}	output clamping current	$V_{\rm O}$ > $V_{\rm CC}$ or $V_{\rm O}$ < 0 V	-	±50	mA
Vo	output voltage	Active mode	[1][2] -0.5	V _{CC} + 0.5	V
		Power-down mode	[1][2] -0.5	+6.5	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
P _{tot}	total power dissipation	T_{amb} = -40 °C to +125 °C	<u>[3]</u>	250	mW
T _{stg}	storage temperature		-65	+150	°C
-					

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		1.65	-	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage	Active mode	0	-	V _{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	-	5.5	V
T _{amb}	ambient temperature		-40	-	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	-	-	20	ns/V
		V_{CC} = 2.7 V to 5.5 V	-	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °	–40 °C to +85 °C			–40 °C to +125 °C	
			Min	Typ <mark>[1]</mark>	Max	Min	Max	
V _{IH}	HIGH-level input	V _{CC} = 1.65 V to 1.95 V	$0.65V_{CC}$	-	-	0.65V _{CC}	-	V
	voltage	V_{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
		V_{CC} = 4.5 V to 5.5 V	0.7V _{CC}	-	-	$0.7V_{CC}$	-	V
V _{IL}	LOW-level input	V_{CC} = 1.65 V to 1.95 V	-	-	$0.35V_{CC}$	-	$0.35V_{CC}$	V
	voltage	V_{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	-	-	0.8	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	V
V _{он}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	output voltage	$I_{O} = -100 \ \mu A;$ $V_{CC} = 1.65 \ V \ to \ 5.5 \ V$	$V_{CC}-0.1$	-	-	$V_{CC}-0.1$	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	0.95	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	1.7	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	1.9	-	V
	$I_{O} = -24$ mA; $V_{CC} = 3.0$ V	2.3	-	-	2.0	-	V	
	$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.8	-	-	3.4	-	V	
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	output voltage	I _O = 100 μA; V _{CC} = 1.65 V to 5.5 V	-	-	0.10	-	0.10	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	-	0.70	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.30	-	0.45	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.40	-	0.60	V
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	-	0.80	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	-	0.80	V
I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	±0.1	±5	-	±100	μA
I _{OFF}	power-off leakage current	$V_{\rm I}~{\rm or}~V_{\rm O}$ = 5.5 V; $V_{\rm CC}$ = 0 V	-	±0.1	±10	-	±200	μA
lcc	supply current	$V_1 = 5.5 V \text{ or GND}; I_0 = 0 A;$ $V_{CC} = 1.65 V \text{ to } 5.5 V$	-	0.1	10	-	200	μA
∆l _{CC}	additional supply current		-	5	500	-	5000	μA
Cı	input capacitance	$V_{CC} = 3.3 \text{ V};$ $V_{I} = \text{GND to } V_{CC}$	-	3	-	-	-	pF

[1] All typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 8.

Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C to +125 °C		Unit
				Min	Typ <mark>[1]</mark>	Max	Min	Max	
t _{pd}	propagation delay	A, B and C to Y; see Figure 7	[2]						
		V_{CC} = 1.65 V to 1.95 V		1.5	4.7	18.0	1.5	21.5	ns
		V_{CC} = 2.3 V to 2.7 V		1.0	3.0	6.5	1.0	7.8	ns
		$V_{CC} = 2.7 V$		1.0	3.0	6.0	1.0	7.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	2.6	5.0	1.0	6.2	ns
		V_{CC} = 4.5 V to 5.5 V		1.0	1.9	3.6	1.0	4.4	ns
C_{PD}	power dissipation capacitance	V_{I} = GND to V_{CC} ; V_{CC} = 3.3 V	[3]	-	12	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma(C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 f_o = output frequency in MHz;

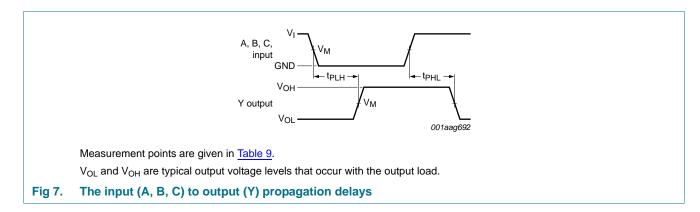
 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of the outputs.

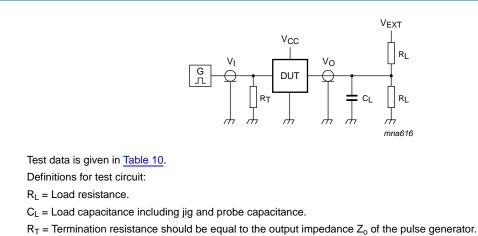
12. Waveforms



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Table 9. Measurement points					
Supply voltage	Input	Output			
V _{CC}	V _M	V _M			
1.65 V to 1.95 V	0.5V _{CC}	0.5V _{CC}			
2.3 V to 2.7 V	0.5V _{CC}	0.5V _{CC}			
2.7 V	1.5 V	1.5 V			
3.0 V to 3.6 V	1.5 V	1.5 V			
4.5 V to 5.5 V	0.5V _{CC}	0.5V _{CC}			



V_{EXT} = External voltage for measuring switching times.

Fig 8. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load		V _{EXT}
V _{cc}	VI	$t_r = t_f$	CL	RL	t _{PLH} , t _{PHL}
1.65 V to 1.95 V	V _{CC}	\leq 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V _{CC}	\leq 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V _{CC}	\leq 2.5 ns	50 pF	500 Ω	open

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Single 3-input NAND gate

13. Package outline

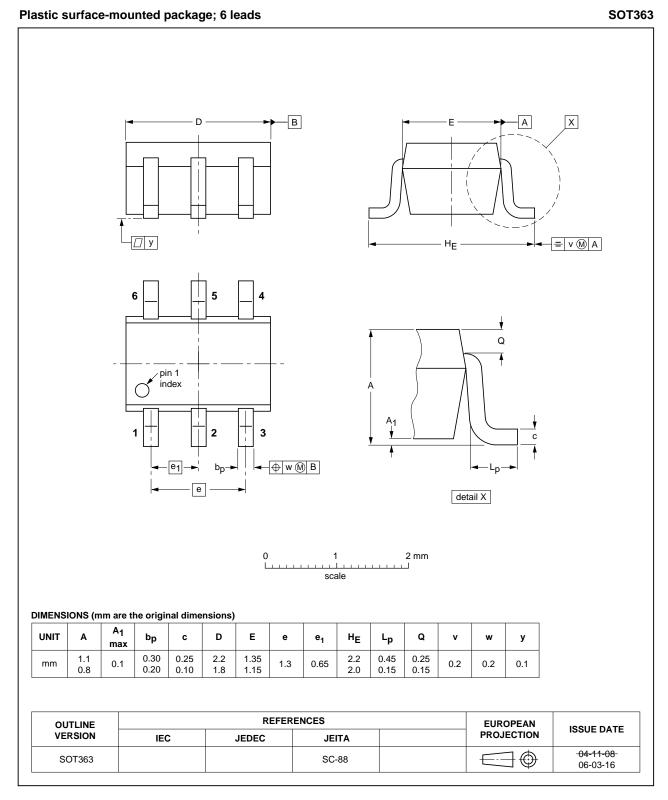


Fig 9. Package outline SOT363 (SC-88)

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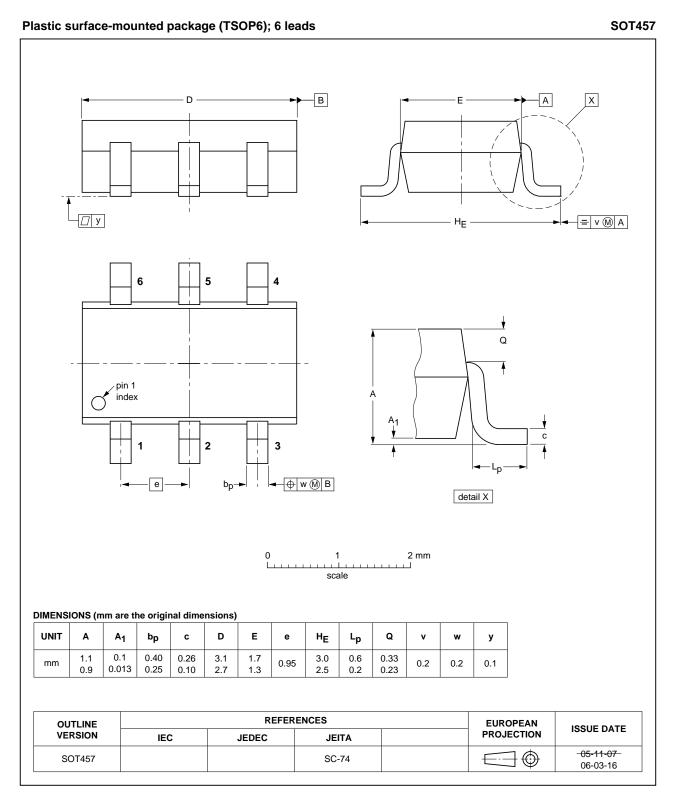
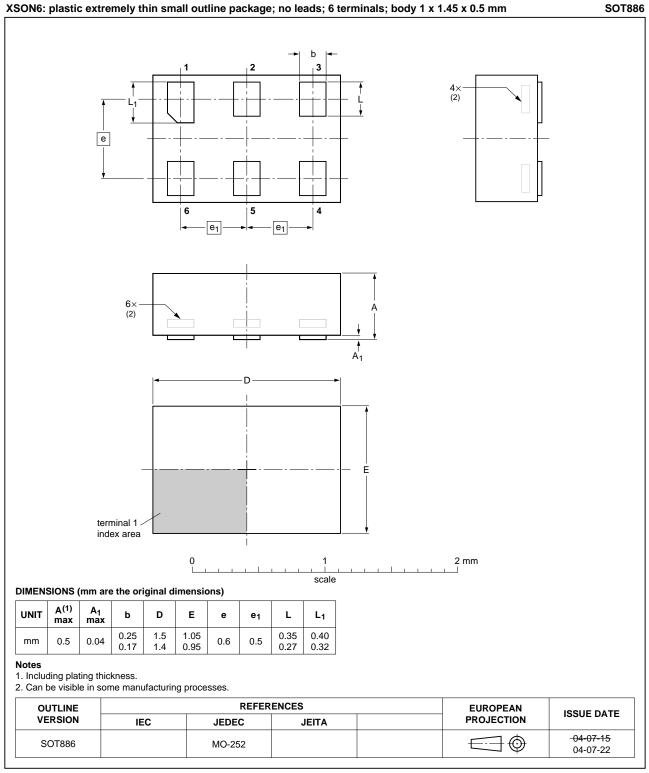


Fig 10. Package outline SOT457 (SC-74)

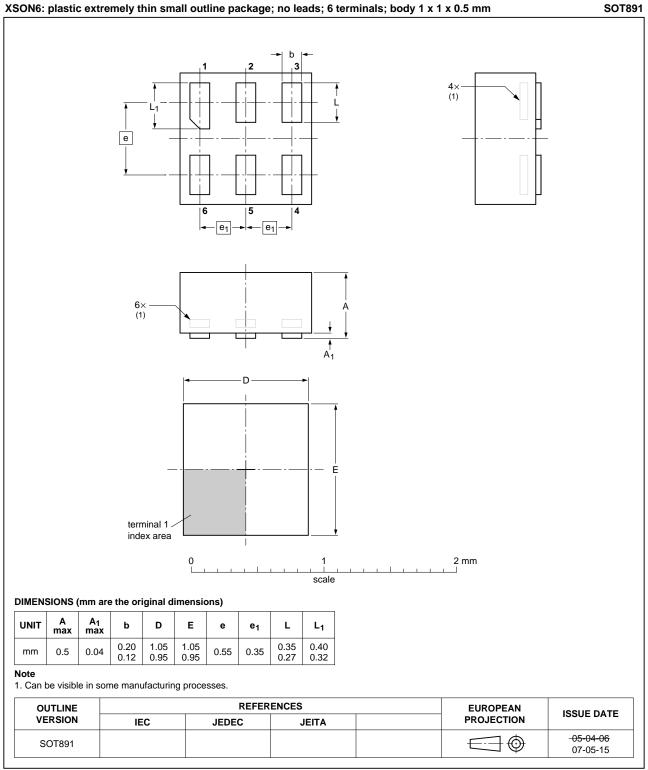
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XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

Fig 11. Package outline SOT886 (XSON6)

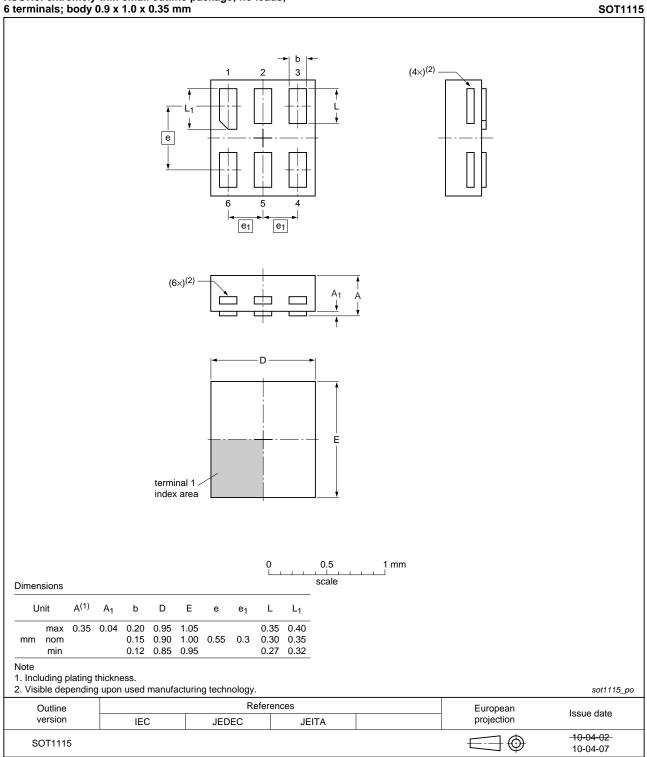
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XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

Fig 12. Package outline SOT891 (XSON6)

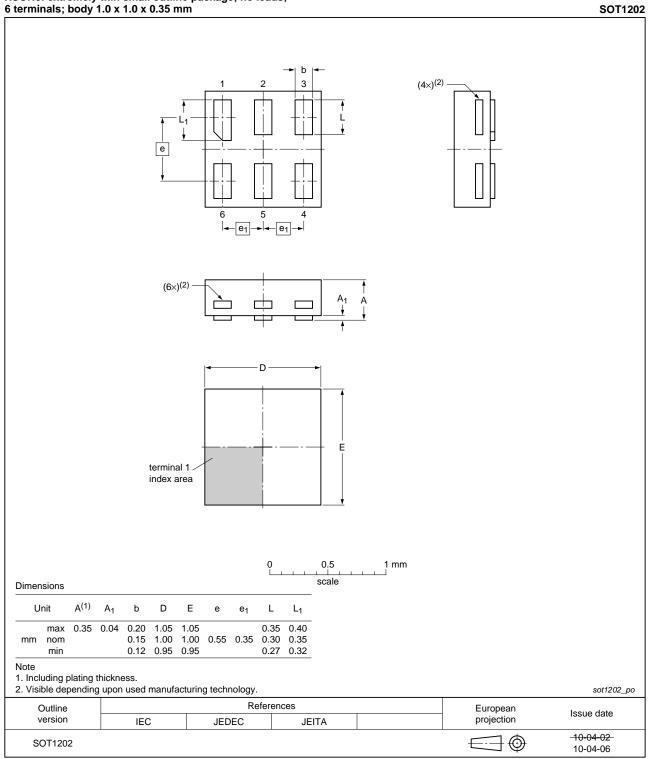
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XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 13. Package outline SOT1115 (XSON6)

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XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 14. Package outline SOT1202 (XSON6)

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14. Abbreviations

Table 11.	Abbreviations
Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

-				
Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G10 v.3	20111208	Product data sheet	-	74LVC1G10 v.2
Modifications:	 Legal pages u 	pdated.		
74LVC1G10 v.2	20101021	Product data sheet	-	74LVC1G10 v.1
74LVC1G10 v.1	20071002	Product data sheet	-	-

16. Legal information

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Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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74LVC1G10

Single 3-input NAND gate

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